

# FDC602P

# P-Channel 2.5V PowerTrench® Specified MOSFET

### **General Description**

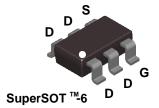
This P-Channel 2.5V specified MOSFET uses a rugged gate version of Fairchild's advanced PowerTrench process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5V – 12V).

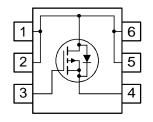
### **Applications**

- Battery management
- Load switch
- · Battery protection

#### **Features**

- -5.5 A, -20 V  $R_{DS(ON)} = 0.035 \Omega @ V_{GS} = -4.5 V$  $R_{DS(ON)} = 0.050 \Omega @ V_{GS} = -2.5 V$
- · Fast switching speed
- High performance trench technology for extremely low  $R_{\mbox{\scriptsize DS(ON)}}$





### Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		-20	V
V <sub>GSS</sub>	Gate-Source Voltage		±12	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	-5.5	А
	- Pulsed		-20	
P <sub>D</sub>	Maximum Power Dissipation	(Note 1a)	1.6	W
		(Note 1b)	0.8	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Tem	perature Range	−55 to +150	°C

### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W

**Package Marking and Ordering Information** 

Device Marking	Device	Reel Size	Tape width	Quantity	
.602	FDC602P	7"	8mm	3000 units	

Electric	cal Characteristics	T <sub>A</sub> = 25°C unless otherwise noted	T	ı		1
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics		•	•		
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-20			V
ΔBV <sub>DSS</sub> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$ , Referenced to 25°C		-14		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V},  V_{GS} = 0 \text{ V}$			-1	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage, Forward	$V_{GS} = 12 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage, Reverse	$V_{GS} = -12 \text{ V},  V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.6	-0.9	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu A$ , Referenced to $25^{\circ}C$		3		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance	$V_{GS} = -4.5 \text{ V},  I_D = -5.5 \text{ A}$ $V_{GS} = -2.5 \text{ V},  I_D = -4.5 \text{ A}$ $V_{GS} = -4.5 \text{ V}, I_D = -5.5 \text{AT}_J = 125^{\circ}\text{C}$		0.027 0.038 0.038	0.035 0.050 0.053	Ω
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, \qquad V_{DS} = -5 \text{ V}$	-20			Α
<b>g</b> FS	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_{D} = -5.5 \text{ A}$		19		S
Dvnamio	Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = -10 \text{ V},  V_{GS} = 0 \text{ V},$		1456		pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		300		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			150		pF
Switchir	ng Characteristics (Note 2)	•			•	•
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = -10 \text{ V}, \qquad I_{D} = -1 \text{ A},$		15	27	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, \qquad R_{GEN} = 6 \Omega$		11	20	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			57	91	ns
t <sub>f</sub>	Turn-Off Fall Time	7		37	59	ns
Qg	Total Gate Charge	$V_{DS} = -10 \text{ V}, \qquad I_{D} = -5.5 \text{ A},$		14	20	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = -4.5 V		3		nC
$Q_{gd}$	Gate-Drain Charge	1		5		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Source				-1.3	Α
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V},  I_S = -1.3 \text{ A}  \text{(Note 2)}$		-0.7	-1.2	V

#### Notes

- a. 78°C/W when mounted on a 1in² pad of 2oz copper on FR-4 board.
- b. 156°C/W when mounted on a minimum pad.
- 2. Pulse Test: Pulse Width  $\leq 300~\mu s,~Duty~Cycle \leq 2.0\%$

<sup>1.</sup>  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.

# **Typical Characteristics**

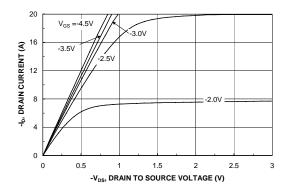


Figure 1. On-Region Characteristics.

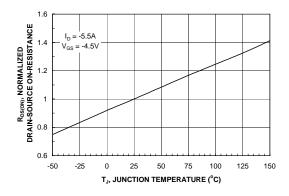


Figure 3. On-Resistance Variation with Temperature.

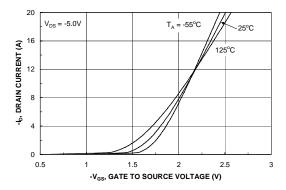


Figure 5. Transfer Characteristics.

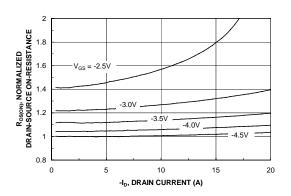


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

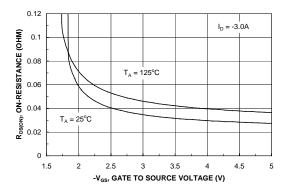


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

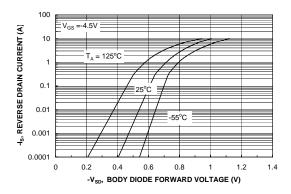
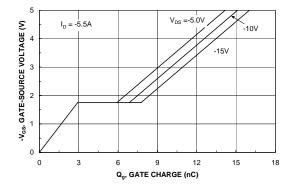


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

# **Typical Characteristics**



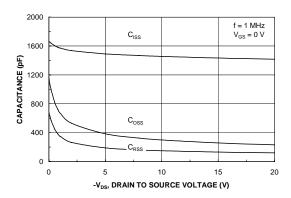
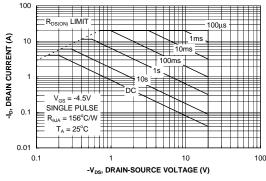


Figure 7. Gate Charge Characteristics.



Figure 8. Capacitance Characteristics.



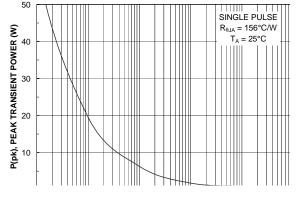


Figure 9. Maximum Safe Operating Area.



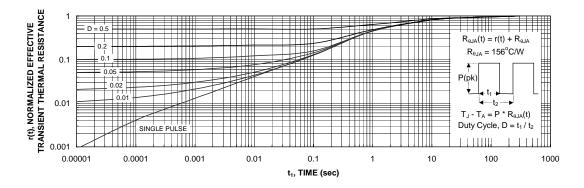
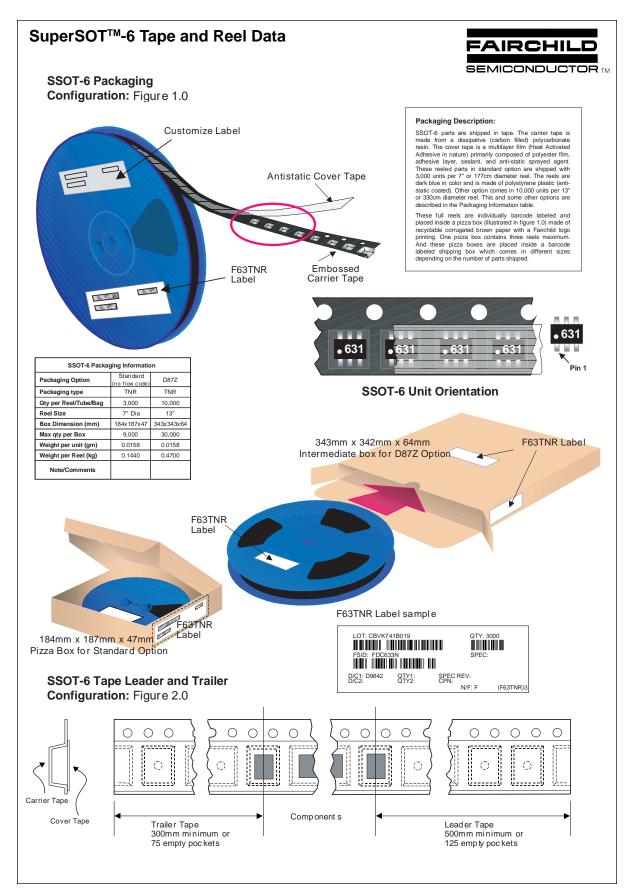


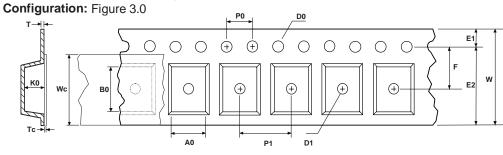
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.





### **SSOT-6 Embossed Carrier Tape**



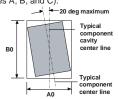


	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-6 (8mm)	3.23 +/-0.10	3.18 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.37 +/-0.10	0.255 +/-0.150	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

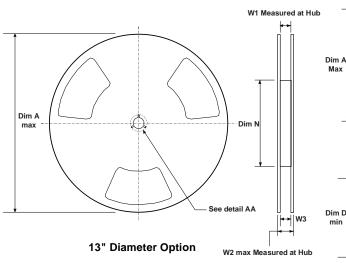


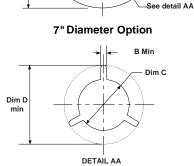
Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

### SSOT-6 Reel Configuration: Figure 4.0



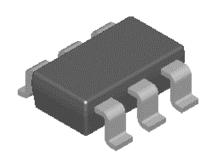


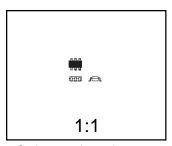
Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

## SuperSOT<sup>™</sup>-6 Package Dimensions



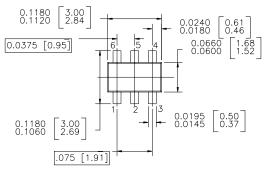
# SuperSOT™-6 (FS PKG Code 31, 33)

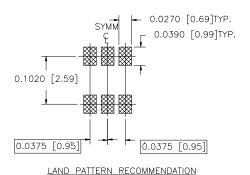




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

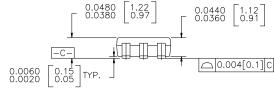
Part Weight per unit (gram): 0.0158

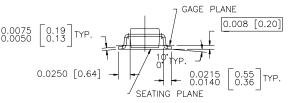




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CONTROLLING DIMENSION IS INCH VALUES IN [ ] ARE MILLIMETERS





NOTES: UNLESS OTHERWISE SPECIFIED

1.0 STANDARD LEAD FINISH : 150 MICROINCHES 93.81 MICROMETERS) MINIMUM TIN / LEAD (SOLDER) ON COPPER.

 $2.0\ \mathsf{NO}\ \mathsf{JEDEC}\ \mathsf{REGISTRATION}\ \mathsf{AS}\ \mathsf{OF}\ \mathsf{JULY}\ 1996$ 

SUPER SOT 6 LEADS

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